L Number	Hits	Search Text	DB	Time stamp
_	1991	<pre>@ad<=20001221 and 'memory' same 'high voltage' same 'logic'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/30 11:28
-	16	<pre>@ad<=20001221 and 'memory' same 'high voltage transistor' same 'logic transistor'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/11 09:03
-	609	@ad<=20001221 and 'memory' with 'high voltage' with 'logic'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/10 16:33
-	488	@ad<=20001221 and (257/314).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/30 13:54
-	1092	@ad<=20001221 and (257/315).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/30 13:54
-	148	@ad<=20001221 and (257/326).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/09/11
-	1441	@ad<=20001221 and (257/316).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/30 13:54
-	295	@ad<=20001221 and (257/317).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/30
-	188	@ad<=20001221 and (257/318).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/30 13:55
-	1340	@ad<=20001221 and (438/257-258).ccls.	-DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/30
-	246	@ad<=20001221 and (438/266).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/30 13:55
_	92	@ad<=20001221 and (438/242).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/30
-	53	@ad<=20001221 and 'memory' and 'HV' adjl 'transistor'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/09/11
_	161	@ad<=20001221 and (438/201).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/09/11 09:17
			DERWENT; IBM_TDB	

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	, 			
-	2	("6287907").PN.	USPAT;	2003/09/11
			US-PGPUB;	09:22
1			EPO; JPO;	
			DERWENT; IBM TDB	
_	2	("6037625").PN.	USPAT;	2003/09/11
		1 0001020 /.211.	US-PGPUB;	09:22
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	("6197635").PN.	USPAT;	2003/09/11
			US-PGPUB;	09:23
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	2	("6194270").PN.	USPAT;	2003/09/11
			US-PGPUB;	09:23
			EPO; JPO;	
			DERWENT;	
		(#F004F10#) Py	IBM_TDB	2002/00/11
-	2	("5904518").PN.	USPAT;	2003/09/11
			US-PGPUB; EPO; JPO;	05:43
			DERWENT;	
			IBM TDB	
_	2	("4719184").PN.	USPAT;	2003/09/11
	'	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	US-PGPUB;	09:23
]		EPO; JPO;	
İ			DERWENT;	
			IBM TDB	<u> </u>
1 -	2	("4471373").PN.	USPAT;	2003/09/11
1			US-PGPUB;	09:23
1			EPO; JPO;	
1	1		DERWENT;	
1			IBM_TDB	0000/65/55
-	256	@ad<=20001221 and (257/315).ccls. and	USPAT;	2003/09/11
		logic and memory	US-PGPUB;	09:29
			EPO; JPO;	
1			DERWENT;	
	14050		IBM_TDB	2003/09/11
-	14959	@ad<=20001221 and logic and memory and	USPAT; US-PGPUB;	09:40
		'high voltage'	EPO; JPO;	05.30
			DERWENT;	
]		IBM TDB	
-		@ad<=20001221 and 'logic' and 'memory	USPAT;	2003/09/11
	[cell' and 'high voltage transistor'	US-PGPUB;	09:42
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	44	@ad<=20001221 and 'memory cell' and	USPĀT;	2003/09/11
		'logic transistor' and 'high voltage	US-PGPUB;	11:06
		transistor'	EPO; JPO;	
İ			DERWENT;	
1			IBM_TDB	
-	470	@ad<=20001221 and 'memory' and 'high	USPAT;	2003/09/11
		voltage transistor' and 'low voltage'	US-PGPUB;	11:09
			EPO; JPO;	
1			DERWENT;	
]		IBM_TDB	2002/00/11
-	304	@ad<=20001221 and 'memory cell' and 'high	USPAT;	2003/09/11 11:35
		voltage transistor' and 'low voltage'	US-PGPUB; EPO; JPO;	11:33
			DERWENT;	
			IBM TDB	
_	90	@ad<=20001221 and 'memory cell' same	USPAT;	2003/09/11
		'high voltage transistor' same 'low	US-PGPUB;	11:36
		voltage'	EPO; JPO;	
			DERWENT;	
			IBM TDB	
L	·			

-	29	@ad<=20001221 and 'memory cell' and 'HV	USPAT;	2004/03/30
		transistor' and 'LV'	US-PGPUB;	13:57
			EPO; JPO;	
			DERWENT; IBM TDB	
_	223	@ad<=20001221 and 'memory cell' and	USPAT;	2003/09/11
	225	'logic transistor'	US-PGPUB;	14:21
			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
-	2	"20030168694"	USPĀT;	2004/03/30
1			US-PGPUB;	11:28
			EPO; JPO;	
			DERWENT;	
1		0-4-20001201 - 3 (257/210) 3	IBM_TDB	2004/02/20
-	218	@ad<=20001221 and (257/319).ccls.	USPAT;	2004/03/30
			US-PGPUB; EPO; JPO;	13:53
			DERWENT;	
1			IBM TDB	
l _	216	@ad<=20001221 and (257/320).ccls.	USPAT;	2004/03/30
	210	- 5 2000-2221 Wild (201/020) 10020 1	US-PGPUB;	13:53
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	738	@ad<=20001221 and (257/321).ccls.	USPAT;	2004/03/30
			US-PGPUB;	13:54
	1		EPO; JPO;	
			DERWENT;	
	224	0-4-20001221 4 /257/2221 3 -	IBM_TDB	2004/03/30
-	204	@ad<=20001221 and (257/322).ccls.	USPAT; US-PGPUB;	2004/03/30
			EPO; JPO;	13:34
			DERWENT;	
			IBM TDB	
_	82	@ad<=20001221 and (257/323).ccls.	USPAT;	2004/03/30
			US-PGPUB;	13:54
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	454	@ad<=20001221 and (257/324).ccls.	USPAT;	2004/03/30
			US-PGPUB;	13:55
			EPO; JPO; DERWENT;	
			IBM TDB	
_	100	 @ad<=20001221_and (257/325).ccls.	USPAT;	2004/03/30
1	1 - 1 - 109		US-PGPUB;	13:55
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	150	@ad<=20001221 and (257/326).ccls.	USPAT;	2004/03/30
1			US-PGPUB;	13:55
			EPO; JPO;	
			DERWENT;	
	400		IBM_TDB USPAT;	2004/03/30
1 -	498	@ad<=20001221 and (257/314).ccls.	US-PGPUB;	13:55
			EPO; JPO;	13.00
			DERWENT;	
			IBM TDB	1
_	1106	@ad<=20001221 and (257/315).ccls.	USPAT;	2004/03/30
		· · · ·	US-PGPUB;	13:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/02/22
-	1453	@ad<=20001221 and (257/316).ccls.	USPAT;	2004/03/30
			US-PGPUB;	13:57
			EPO; JPO; DERWENT;	
			IBM TDB	
		<u></u>	T T DIT T D D	<u> </u>

-	298	@ad<=20001221 and (257/317).ccls.	USPAT;	2004/03/30
			US-PGPUB;	13:57
			EPO; JPO;	
			DERWENT;	=
			IBM_TDB	0004/00/00
-	193	@ad<=20001221 and (257/318).ccls.	USPAT;	2004/03/30
			US-PGPUB;	13:58
1			EPO; JPO;	
			DERWENT;	
		0 1 00001001 1 (100 (055 050) 3	IBM_TDB	0004/02/20
-	1352	@ad<=20001221 and (438/257-258).ccls.	USPAT;	2004/03/30
			US-PGPUB;	13:59
			EPO; JPO;	
		,	DERWENT;	
	0.50	0 1: 00001001	IBM_TDB USPAT;	2004/02/20
-	250	@ad<=20001221 and (438/266).ccls.	US-PGPUB;	2004/03/30
			EPO; JPO;	13:59
			DERWENT;	
i			IBM TDB	
		0-14 20001221 1 (420/242) 1-	USPAT;	2004/03/30
-	94	@ad<=20001221 and (438/242).ccls.	US-PGPUB;	13:59
			EPO; JPO;	13.39
1			DERWENT;	
	1		IBM TDB	
	46	@ad<=20001221 and 'memory cell' and 'High	USPAT;	2004/03/30
-	46		US-PGPUB;	14:00
		voltage transistor' and 'Logic transistor'	EPO; JPO;	13.00
		transistor	DERWENT;	·
Į.			IBM TDB	
	4	(("5793673") or ("5792670")).PN.	USPAT;	2004/03/30
-	4	((5/936/3) OI (5/926/0)).FN.	US-PGPUB;	14:00
	ļ		EPO; JPO;	11.00
			DERWENT;	
			IBM TDB	
	2	@ad<=20001221 and 'memory cell' and 'HV'	USPAT;	2004/03/30
-		with 'transistor' and 'Logic transistor'	US-PGPUB;	14:01
		With transficor and bogic transficor	EPO; JPO;	
			DERWENT;	
			IBM TDB	,
_	45	@ad<=20001221 and 'memory cell' and 'HV'	USPAT;	2004/03/30
		with 'transistor' and 'LV' with	US-PGPUB;	14:01
		'transistor'	EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
] -	146	@ad<=20001221 and 'memory cell' and 'high	USPAT;	2004/03/30
1		voltage transistor' and 'low voltage	US-PGPUB;	16:23
		transistor'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	362	@ad<=20001221 and 'FLOTOX'	USPAT;	2004/03/30
			US-PGPUB;	15:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0		USPAT;	2004/03/30
		voltage transistor' and 'low voltage	US-PGPUB;	16:24
		transistor'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/02/22
_	10	@ad<=20001221 and 'EEPPROM' and 'high	USPAT;	2004/03/30
		voltage transistor' and 'low voltage	US-PGPUB;	16:25
		transistor'	EPO; JPO;	
			DERWENT;	
	1	0-44-20001221 and IRREPROVE and LIRE and	IBM_TDB USPAT;	2004/03/30
-	0	¥ · · · · · · · · · · · · · · · · · ·	US-PGPUB;	16:26
1		'LV'	EPO; JPO;	10.20
			DERWENT;	
			IBM TDB	
1			1 1 DE 1 1 DE	

-	21	@ad<=20001221	and	'flash	memory'	and	'HV'	USPAT;	2004/03/30
		and 'LV'						US-PGPUB;	16:26
								EPO; JPO;	
								DERWENT;	
	İ							IBM TDB	